

Fast Settling, JFET Input **Operational Amplifier**

LT1122

FEATURES

| 100% Teste | 340ns Typ | | |
|--------------|---------------|-------------|------------|
| to 1mV at S | um Node, 10∖ | / Step | 540ns Max |
| Tested with | Fixed Feedbac | k Capacitor | |
| Slew Rate | | - | 60V/µs Min |
| Gain-Bandw | idth Product | | 14MHz |
| Power Band | 1.2 MHz | | |
| Unity-Gain | Stable; Phase | Margin | 60° |
| Input Offset | : Voltage | | 600µV Max |
| Input Bias (| Current | 25°C | 75pA Max |
| | | 70°C | 600pA Max |
| Input Offset | Current | 25°C | 40pA Max |
| | | 70°C | 150pA Max |
| | | | |

Low Distortion

APPLICATIONS

- Fast 12-Bit D/A Output Amplifiers
- High Speed Buffers
- Fast Sample-and-Hold Amplifiers
- High Speed Integrators
- Voltage to Frequency Converters
- Active Filters
- Log Amplifiers
- Peak Detectors

TYPICAL APPLICATION

12-Bit Voltage Output D/A Converter



(DEPENDING ON D/A CONVERTER USED)



The LT®1122 JFET input operational amplifier combines high speed and precision performance.

A unique poly-gate JFET process minimizes gate series resistance and gate-to-drain capacitance, facilitating wide bandwidth performance, without degrading JFET transistor matching.

It slews at 80V/µs and settles in 340ns. The LT1122 is internally compensated to be unity-gain stable, yet it has a bandwidth of 14MHz at a supply current of only 7mA. Its speed makes the LT1122 an ideal choice for fast settling 12-bit data conversion and acquisition systems.

The LT1122 offset voltage of 120µV, and voltage gain of 500,000 also support the 12-bit accurate applications.

The input bias current of 10pA and offset current of 4pA combined with its speed allow the LT1122 to be used in such applications as high speed sample and hold amplifiers, peak detectors, and integrators.

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Large-Scale Response

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ABSOLUTE MAXIMUM RATINGS (Note 1)

| Supply Voltage | ±20V |
|---------------------------------------|------------|
| Differential Input Voltage | ±40V |
| Input Voltage | ±20V |
| Output Short Circuit Duration | Indefinite |
| Lead Temperature (Soldering, 10 sec.) | |
| | |

PIN CONFIGURATION



ORDER INFORMATION

| LEAD FREE FINISH | TAPE AND REEL | PART MARKING | PACKAGE DESCRIPTION | TEMPERATURE RANGE | | | |
|------------------|------------------|--------------|---------------------|-------------------|--|--|--|
| LT1122ACN8#PBF | LT1122ACN8#TRPBF | LT1122ACN8 | 8-Lead Plastic DIP | -40°C to 85°C | | | |
| LT1122BCN8#PBF | LT1122BCN8#TRPBF | LT1122BCN8 | 8-Lead Plastic DIP | -40°C to 85°C | | | |
| LT1122CCN8#PBF | LT1122CCN8#TRPBF | LT1122CCN8 | 8-Lead Plastic DIP | -40°C to 85°C | | | |
| LT1122DCN8#PBF | LT1122DCN8#TRPBF | LT1122DCN8 | 8-Lead Plastic DIP | -40°C to 85°C | | | |
| LT1122CS8#PBF | LT1122CS8#TRPBF | 11220 | 8-Lead Plastic SO | -40°C to 85°C | | | |
| LT1122DS8#PBF | LT1122DS8#TRPBF | 1122D | 8-Lead Plastic SO | -40°C to 85°C | | | |
| OBSOLETE PACKAGE | | | | | | | |
| LT1122AMJ8#PBF | LT1122AMJ8#TRPBF | LT1122AMJ8 | 8-Lead Hermetic DIP | –55°C to 125°C | | | |
| LT1122BMJ8#PBF | LT1122BMJ8#TRPBF | LT1122BMJ8 | 8-Lead Hermetic DIP | -55°C to 125°C | | | |
| LT1122CMJ8#PBF | LT1122CMJ8#TRPBF | LT1122CMJ8 | 8-Lead Hermetic DIP | -55°C to 125°C | | | |
| LT1122DMJ8#PBF | LT1122DMJ8#TRPBF | LT1122DMJ8 | 8-Lead Hermetic DIP | –55°C to 125°C | | | |
| LT1122ACJ8#PBF | LT1122ACJ8#TRPBF | LT1122ACJ8 | 8-Lead Hermetic DIP | -40°C to 85°C | | | |
| LT1122BCJ8#PBF | LT1122BCJ8#TRPBF | LT1122BCJ8 | 8-Lead Hermetic DIP | -40°C to 85°C | | | |
| LT1122CCJ8#PBF | LT1122CCJ8#TRPBF | LT1122CCJ8 | 8-Lead Hermetic DIP | -40°C to 85°C | | | |
| LT1122DCJ8#PBF | LT1122DCJ8#TRPBF | LT1122DCJ8 | 8-Lead Hermetic DIP | -40°C to 85°C | | | |

Consult LTC Marketing for parts specified with wider operating temperature ranges.

Consult LTC Marketing for information on nonstandard lead based finish parts.

For more information on lead free part markings, go to: http://www.linear.com/leadfree/ For more information on tape and reel specifications, go to: http://www.linear.com/tapeandreel/



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ELECTRICAL CHARACTERISTICS The \bullet denotes the specifications which apply over the full operating temperature range, otherwise specifications are at T_A = 25°C. V_S = ±15V, V_{CM} = 0V unless otherwise noted. (Note 2)

| 0////00/ | | | LT | 122AM 1122AC | /BC | LT [.] | 122CM/ 1122CC/ 1122CS/ | DC DS | |
|------------------|---|---|--------------|--|-----|-----------------|--|----------|-------------------|
| SYMBOL | PARAMETER | CONDITIONS | MIN | | MAX | MIN | TYP | MAX | UNITS |
| V _{OS} | Input Offset Voltage | | | 120 | 600 | | 130 | 900 | μV |
| l _{os} | Input Offset Current | | | 4 | 40 | | 5 | 50 | рА |
| IB | Input Bias Current | | | 10 | 75 | | 12 | 100 | рА |
| | Input Resistance Differential Common Mode | V _{CM} = -10V to 8V V _{CM} = 8V to 11V | | 10 ¹² 10 ¹² 10 ¹¹ | | | 10 ¹² 10 ¹² 10 ¹¹ | | Ω Ω Ω |
| | Input Capacitance | | | 4 | | | 4 | | pF |
| SR | Slew Rate | $A_V = -1$ | 60 | 80 | | 50 | 75 | | V/µs |
| | Settling Time (Note 2) | 10V to 0V, –10V to 0V 100% Tested: A- and C-Grades to 1mV at Sum Node B- and D-Grades to 1mV at Sum Node All Grades to 0.5mV at Sum Node | | 340 350 450 | 540 | | 350 360 470 | 590 | ns ns ns |
| GBW | Gain-Bandwidth Product Power Bandwidth | V _{OUT} = 20V _{P-P} | | 14 1.2 | | | 13 1.1 | | MHz MHz |
| A _{VOL} | Large-Signal Voltage Gain | $V_{OUT} = \pm 10V, R_L = 2k\Omega$ $V_{OUT} = \pm 10V, R_L = 600\Omega$ | 180 130 | 500 250 | | 150 110 | 450 220 | | V/mV V/mV |
| CMRR | Common-Mode Rejection Ratio | $V_{CM} = \pm 10V$ | 83 | 99 | | 80 | 98 | | dB |
| | Input Voltage Range | (Note 4) | ±10.5 | ±11 | | ±10.5 | ±11 | | V |
| PSRR | Power Supply Rejection Ratio | $V_{\rm S} = \pm 10 V \text{ to } \pm 18 V$ | 86 | 103 | | 82 | 101 | | dB |
| | Input Noise Voltage | 0.1Hz to 10Hz | | 3.0 | | | 3.3 | | μV _{P-P} |
| | Input Noise Voltage Density | $f_0 = 100$ Hz $f_0 = 10$ KHz | | 25 14 | | | 27 15 | | nV/√Hz nV/√Hz |
| | Input Noise Current Density | f ₀ = 100Hz, f ₀ = 10kHz | | 2 | | | 2 | | fA/√Hz |
| V _{OUT} | Output Voltage Swing | $ \begin{array}{l} R_{L} = 2 k \Omega \\ R_{L} = 600 \Omega \end{array} $ | ±12 ±11.5 | ±12.5 ±12 | | ±12 ±11.5 | ±12.5 ±12 | | V V |
| I _S | Supply Current | | | 7.5 | 10 | | 7.8 | 11 | mA |
| | Minimum Supply Voltage | (Note 5) | ±5 | | | ±5 | | | V |
| | Offset Adjustment Range | $R_{POT} \ge 10k$, Wiper to V ⁺ | ±4 | ±10 | | ±4 | ±10 | | mV |



ELECTRICAL CHARACTERISTICS The \bullet denotes the specifications which apply over the full operating temperature range, otherwise specifications are at 0°C $\leq T_A \leq 70$ °C. V_S = ±15V, V_{CM} = 0V. (Note 2)

| | | | | LT | 1122AC/ | BC | 1 | 1122CC/ 1122CS/ | | |
|------------------|--|---------------------------------------|---|-------|---------|------|-------|--------------------|------|-------|
| SYMBOL | PARAMETER | CONDITIONS | | MIN | ТҮР | MAX | MIN | TYP | MAX | UNITS |
| V _{OS} | Input Offset Voltage | | • | | 350 | 1400 | | 400 | 2000 | μV |
| | Average Temperature Coefficient of Input Offset Voltage | | • | | 5 | 18 | | 6 | 25 | µV/°C |
| I _{OS} | Input Offset Current | | • | | 12 | 150 | | 15 | 200 | pА |
| IB | Input Bias Current | | • | | 80 | 600 | | 90 | 800 | pА |
| A _{VOL} | Large-Signal Voltage Gain | $V_{OUT} = \pm 10V, R_L \ge 2k\Omega$ | • | 120 | 380 | | 100 | 340 | | V/mV |
| CMRR | Common-Mode Rejection Ratio | $V_{CM} = \pm 10V$ | • | 82 | 98 | | 78 | 96 | | dB |
| PSRR | Power Supply Rejection Ratio | V _S = ±10V to ±17V | • | 84 | 101 | | 80 | 99 | | dB |
| | Input Voltage Range | | • | ±10 | ±10.8 | | ±10 | ±10.8 | | V |
| V _{OUT} | Output Voltage Swing | $R_L = 2k\Omega$ | • | ±11.5 | ±12.4 | | ±11.5 | ±12.4 | | V |
| SR | Slew Rate | $A_V = -1$ | • | 50 | 70 | | 40 | 65 | | V/µs |

The • denotes the specifications which apply over the full operating temperature range, otherwise specifications are at $-55^{\circ}C \le T_A \le 125^{\circ}C$. $V_S = \pm 15V$, $V_{CM} = 0V$. (Note 2)

| | | | | LT1122AM/BM | | | LT | | | |
|------------------|--|---------------------------------------|---|-------------|-------|------|-------|-------|------|-------|
| SYMBOL | PARAMETER | CONDITIONS | | MIN | TYP | MAX | MIN | ТҮР | MAX | UNITS |
| V _{OS} | Input Offset Voltage | | • | | 650 | 2400 | | 800 | 3400 | μV |
| | Average Temperature Coefficient of Input Offset Voltage | | • | | 6 | 18 | | 7 | 25 | µV/°C |
| I _{OS} | Input Offset Current | | • | | 0.5 | 6 | | 0.6 | 9 | nA |
| I _B | Input Bias Current | | • | | 6 | 25 | | 7 | 35 | nA |
| A _{VOL} | Large-Signal Voltage Gain | $V_{OUT} = \pm 10V, R_L \ge 2k\Omega$ | • | 70 | 230 | | 60 | 200 | | V/mV |
| CMRR | Common-Mode Rejection Ratio | $V_{CM} = \pm 10V$ | • | 80 | 97 | | 76 | 94 | | dB |
| PSRR | Power Supply Rejection Ratio | $V_{\rm S} = \pm 10$ V to ± 17 V | • | 83 | 100 | | 78 | 98 | | dB |
| | Input Voltage Range | | • | ±10 | ±10.5 | | ±10 | ±10.5 | | V |
| V _{OUT} | Output Voltage Swing | $R_L = 2k\Omega$ | • | ±11.3 | ±12.1 | | ±11.3 | ±12.1 | | V |
| SR | Slew Rate | $A_{V} = -1$ | • | 45 | 60 | | 35 | 55 | | V/µs |

The \bullet denotes the specifications which apply over the full operating temperature range, otherwise specifications are at -40°C \leq T_A \leq 85°C. V_S = ±15V, V_{CM} = 0V. (Note 6)

| | | | | LT1122AM/BM | | | LT | | | |
|------------------|---|---------------------------------------|---|-------------|-------|------|-------|-------|------|-------|
| SYMBOL | PARAMETER | CONDITIONS | | MIN | ТҮР | MAX | MIN | TYP | MAX | UNITS |
| V _{OS} | Input Offset Voltage | | • | | 450 | 1900 | | 500 | 2700 | μV |
| | Average Temperature Coefficient of Input Offset Voltage | | • | | 6 | 20 | | 7 | 28 | µV/°C |
| l _{os} | Input Offset Current | | • | | 30 | 600 | | 40 | 900 | pА |
| I _B | Input Bias Current | | • | | 230 | 2000 | | 260 | 2700 | pА |
| A _{VOL} | Large-Signal Voltage Gain | $V_{OUT} = \pm 10V, R_L \ge 2k\Omega$ | • | 95 | 340 | | 80 | 300 | | V/mV |
| CMRR | Common-Mode Rejection Ratio | $V_{CM} = \pm 10V$ | • | 80 | 98 | | 76 | 96 | | dB |
| PSRR | Power Supply Rejection Ratio | V _S = ±10V to ±17V | • | 83 | 100 | | 78 | 98 | | dB |
| | Input Voltage Range | | • | ±10 | ±10.6 | | ±10 | ±10.6 | | V |
| V _{OUT} | Output Voltage Swing | $R_L = 2k\Omega$ | • | ±11.3 | ±12.2 | | ±11.3 | ±12.2 | | V |
| SR | Slew Rate | A _V = -1 | • | 45 | 60 | | 35 | 60 | | V/µs |





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ELECTRICAL CHARACTERISTICS

Note 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

Note 2: The LT1122 is measured in an automated tester in less than one second after application of power. Depending on the package used, power dissipation, heat sinking, and air flow conditions, the fully warmed up chip temperature can be 10°C to 50°C higher than the ambient temperature.

Note 3: Settling time is 100% tested for A- and C-grades using the settling time test circuit shown. This test is not included in quality assurance sample testing.

Note 4: Input voltage range functionality is assured by testing offset voltage at the input voltage range limits to a maximum of 4mV (A, B grades), to 5.7mV (C, D grades).

Note 5: Minimum supply voltage is tested by measuring offset voltage to 7mV maximum at $\pm 5V$ supplies.

Note 6: The LT1122 is not tested and not quality-assurance-sampled at -40°C and at 85°C. These specifications are guaranteed by design, correlation and/or inference from -55°C, 0°C, 25°C, 70°C and/or 125°C tests.



Settling Time Test Fixture



TYPICAL PERFORMANCE CHARACTERISTICS



Settling Time (Input from OV to -10V)





Large-Signal Response

5V/DIV

5V

 $A_V = 1$





Undistorted Output Swing vs Frequency





Gain, Phase vs Frequency

200ns

1122 G05

80

200ns/DIV



Common-Mode Rejection vs Frequency





TYPICAL PERFORMANCE CHARACTERISTICS





APPLICATIONS INFORMATION

Settling Time Measurements

Settling time test circuits shown on some competitive devices' data sheets require:

- 1. A "flat top" pulse generator. Unfortunately, flat top pulse generators are not commercially available.
- A variable feedback capacitor around the device under test. This capacitor varies over a four-to-one range. Presumably, as each op amp is measured for settling time, the capacitor is fine tuned to optimize settling time for that particular device.
- 3. A small inductor load to optimize settling.

The LT1122's settling time is 100% tested in the test circuit shown. No "flat top" pulse generator is required. The test circuit can be readily constructed, using commercially available ICs. Of course, standard high frequency board construction techniques should be followed. All LT1122s are measured with a constant feedback capacitor. No fine tuning is required.

Speed Boost/Overcompensation Terminal

Pin 8 of the LT1122 can be used to change the input stage operating current of the device. Shorting Pin 8 to the positive supply (Pin 7) increases slew rate and bandwidth by about 25%, but at the expense of a reduction in phase margin by approximately 18 degrees. Unity-gain capacitive load handling decreases from typically 500pF to 100pF.

Conversely, connecting a 15k resistor from Pin 8 to ground pulls 1mA out of Pin 8 (with V⁺ = 15V). This reduces slew rate and bandwidth by 25%. Phase margin and capacitive load handling improve; the latter typically increasing to 800pF.

High Speed Operation

As with most high speed amplifiers, care should be taken with supply decoupling, lead dress and component placement.

The power supply connections to the LT1122 must maintain a low impedance to ground over a bandwidth of 20MHz. This is especially important when driving a significant resistive or capacitive load, since all current delivered to the load comes from the power supplies. Multiple high quality bypass capacitors are recommended for each power supply line in any critical application. A 0.1 μ F ceramic and a 1 μ F electrolytic capacitor, as shown, placed as close as possible to the amplifier (with short lead lengths to power supply common) will assure adequate high frequency bypassing, in most applications.



When the feedback around the op amp is resistive (R_F), a pole will be created with R_F, the source resistance and capacitance (R_S, C_S), and the amplifier input capacitance (C_{IN} \approx 4pF). In low closed-loop gain configurations and with R_S and R_F in the kilohm range, this pole can create excess phase shift and even oscillation. A small capacitor (C_F) in parallel with R_F eliminates this problem. With R_S (C_S + C_{IN}) = R_FC_F, the effect of the feedback pole is completely removed.







TYPICAL APPLICATIONS







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PACKAGE DESCRIPTION

Please refer to http://www.linear.com/designtools/packaging/ for the most recent package drawings.



N Package 8-Lead PDIP (Narrow .300 Inch)

NOTE:

1. DIMENSIONS ARE MILLIMETERS

*THESE DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED .010 INCH (0.254mm)



PACKAGE DESCRIPTION

Please refer to http://www.linear.com/designtools/packaging/ for the most recent package drawings.





PACKAGE DESCRIPTION

Please refer to http://www.linear.com/designtools/packaging/ for the most recent package drawings.



S8 Package





REVISION HISTORY (Revision history begins at Rev B)

| REV | DATE | DESCRIPTION | PAGE NUMBER |
|-----|-------|--|-------------|
| В | 02/14 | Updated data sheet to current standards. New Order Information Table, Package Descriptions | 2, 10-12 |



TYPICAL APPLICATION





RELATED PARTS

| PART NUMBER | DESCRIPTION | COMMENTS |
|-----------------------|-----------------------------------|---|
| LT1022 | High Speed Precision JFET Op Amp | 23V/µs Min Slew Rate, 250µV V _{OS} |
| LT1055/LT1056 | Precision High Speed JFET Op Amps | 16V/μs Slew Rate, 150μV V _{OS} |
| LT1464 | 1MHz C-Load™ Stable JFET Op Amp | Capacitive Loads Up to 10nF |
| LTC [®] 6244 | 50MHz Low Noise CMOS Op Amp | 1pA I _B , 100µV Max V _{OS} , 1.5µV _{P-P} , 0.1Hz to 10Hz Noise |

